Mehmet Ã¶ztÃ¼rk

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/9059111/publications.pdf

Version: 2024-02-01

		759055	395590
42	1,274	12	33
papers	citations	h-index	g-index

42	42	42	1604
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Energy Harvesting and Storage with Soft and Stretchable Materials. Advanced Materials, 2021, 33, e2004832.	11.1	91
2	Flexible thermoelectric generator with liquid metal interconnects and low thermal conductivity silicone filler. Npj Flexible Electronics, 2021, 5, .	5.1	44
3	Energy Harvesting and Storage: Energy Harvesting and Storage with Soft and Stretchable Materials (Adv. Mater. 19/2021). Advanced Materials, 2021, 33, 2170151.	11.1	1
4	Flexible thermoelectric generators for body heat harvesting â€“ Enhanced device performance using high thermal conductivity elastomer encapsulation on liquid metal interconnects. Applied Energy, 2020, 262, 114370.	5.1	113
5	High Thermal Conductivity Silicone Elastomer Doped with Graphene Nanoplatelets and Eutectic GaIn Liquid Metal Alloy. ECS Journal of Solid State Science and Technology, 2019, 8, P357-P362.	0.9	37
6	Flexible thermoelectric generator using bulk legs and liquid metal interconnects for wearable electronics. Applied Energy, 2017, 202, 736-745.	5.1	260
7	Designing thermoelectric generators for self-powered wearable electronics. Energy and Environmental Science, 2016, 9, 2099-2113.	15.6	299
8	Flexible Technologies for Self-Powered Wearable Health and Environmental Sensing. Proceedings of the IEEE, 2015, 103, 665-681.	16.4	166
9	Schottky Barrier Height of Erbium Silicide on $ hbox{Si}_{1 - x}hbox{C}_{x}$. IEEE Electron Device Letters, 2009, 30, 949-951.	2.2	6
10	Schottky Barrier Height of Nickel Silicide Contacts Formed on $hbox{Si}_{1 - x}hbox{C}_{x}$ Epitaxial Layers. IEEE Electron Device Letters, 2009, 30, 1320-1322.	2.2	2
11	Platinum Germanosilicide Contacts Formed on Strained and Relaxed $hbox{Si}_{1 - x}hbox{Ge}_{x}$ Layers. IEEE Transactions on Electron Devices, 2009, 56, 1220-1227.	1.6	8
12	Tuning of the Platinum Silicide Schottky Barrier Height on n-Type Silicon by Sulfur Segregation. IEEE Electron Device Letters, 2009, 30, 331-333.	2.2	31
13	Tuning of the Nickel Silicide Schottky Barrier Height on p-Type Silicon by Indium Implantation. IEEE Electron Device Letters, 2009, 30, 1272-1274.	2.2	23
14	Impact of Heavy Boron Doping and Nickel Germanosilicide Contacts on Biaxial Compressive Strain in Pseudomorphic Silicon-Germanium Alloys on Silicon. Materials Research Society Symposia Proceedings, 2006, 913, 1.	0.1	0
15	Impact of Ge on integration of HfO2 and metal gate electrodes on strained Si channels. Applied Physics Letters, 2005, 87, 071903.	1.5	7
16	Source/Drain Junctions and Contacts for 45 nm CMOS and Beyond. AIP Conference Proceedings, 2005, , .	0.3	8
17	Low Resistivity Nickel Germanosilicide Contacts to Ultra-shallow Junctions Formed by the Selective Si1-xGexTechnology for Nanoscale CMOS. Materials Research Society Symposia Proceedings, 2003, 765, 1.	0.1	0
18	Nickel, Platinum and Zirconium Germanosilicide Contacts to Heavily Phosphorous Doped Silicon-Germanium Alloys for Advanced CMOS Source/Drain Junctions. Materials Research Society Symposia Proceedings, 2002, 745, 4111.	0.1	2

#	Article	IF	Citations
19	Low Thermal Budget In Situ Surface Cleaning for Selective Silicon Epitaxy. Journal of the Electrochemical Society, 1998, 145, 3602-3609.	1.3	5
20	IS Selective CVD an Improvement for the Titanium Silicide Process in Sub-Quarter Micron Technology? A Phase Formation Study Using X-ray Diffraction. Materials Research Society Symposia Proceedings, 1998, 514, 243.	0.1	1
21	Is Selective Cvd an Improvement for the Titanium Silicide Process in Sub-Quarter Micron Technology? A Phase Formation Study Using X-Ray Diffraction. Materials Research Society Symposia Proceedings, 1998, 514, 439.	0.1	1
22	Selective Rapid Thermal Chemical Vapor Deposition of Titanium Disilicide on Silicon and Polysilicon. Materials Research Society Symposia Proceedings, 1997, 470, 139.	0.1	0
23	Silicon Nucleation and Film Evolution on Silicon Dioxide Using Disilane: Rapid Thermal Chemical Vapor Deposition of Very Smooth Silicon at High Deposition Rates. Journal of the Electrochemical Society, 1996, 143, 649-657.	1.3	9
24	Characterization of MOS Devices Fabricated on Carbon Implanted Silicon Substrates. Materials Research Society Symposia Proceedings, 1995, 378, 737.	0.1	0
25	Low Temperature Selective Silicon Epitaxy Using Si2H6, H2 and Cl2 in Ultra High Vacuum Rapid Thermal Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1995, 387, 335.	0.1	0
26	Formation of Raised Source/Drain Junctions by Rapid Thermal Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1995, 387, 355.	0.1	2
27	Formation of Ultra-Shallow Junctions in Silicon by Rapid Thermal Vapor Phase Doping in an Ultrahigh Vacuum Rapid Thermal Processing System. Materials Research Society Symposia Proceedings, 1995, 387, 395.	0.1	0
28	Silicon Etching in Rapid Thermal Chemical Vapor Deposition of Tisi2. Materials Research Society Symposia Proceedings, 1995, 387, 443.	0.1	1
29	Growth Kinetics, Silicon Nucleation on Silicon Dioxide, and Selective Epitaxy Using Disilane and Hydrogen in an Ultrahigh Vacuum Rapid Thermal Chemical Vapor Deposition Reactor. Journal of the Electrochemical Society, 1994, 141, 3269-3273.	1.3	35
30	Influence of dry and wet cleaning on the properties of rapid thermal grown and deposited gate dielectrics. Journal of Electronic Materials, 1993, 22, 335-339.	1.0	13
31	Low temperature silicon epitaxy in an ultrahigh vacuum rapid thermal chemical vapor deposition reactor using disilane. Applied Physics Letters, 1993, 63, 1225-1227.	1.5	16
32	Application of Constant Absorptivity Ring (Car) to Improve Polysilicon Thickness Uniformity In A Rapid Thermal Chemical Vapor Deposition Reactor. Materials Research Society Symposia Proceedings, 1993, 303, 19.	0.1	0
33	High Quality Silicon Epitaxy In An Ultra High Vacuum Rapid Thermal Cvd Reactor: An Application to Single Wafer Processing. Materials Research Society Symposia Proceedings, 1993, 303, 25.	0.1	1
34	A Novel Implantation Free Raised Source/Drain Mosfet Process Using Selective Rapid Thermal Chemical Vapor Deposition Of In-Situ Boron Doped Si_xGe_{1-x}. Materials Research Society Symposia Proceedings, 1993, 303, 37.	0.1	1
35	Characterization of Oxygen-Doped and Non-Oxygen-Doped Polysilicon Films Prepared by Rapid Thermal Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1993, 303, 49.	0.1	2
36	Self-Aligned Formation of C54 Titanium Germanosilicide Using Rapid Thermal Processing and Application to Raised, Ultrashallow Junctions. Materials Research Society Symposia Proceedings, 1993, 320, 311.	0.1	2

#	Article	IF	Citations
37	Cleaning during Initial Stages of Epitaxial Growth in an Ultrahigh Vacuum Rapid Thermal Chemical Vapor Deposition Reactor. Materials Research Society Symposia Proceedings, 1993, 334, 463.	0.1	0
38	Silicon Nucleation on Silicon Dioxide and Selective Epitaxy In An Ultra-High Vacuum Raptid Thermal Chemical Vapor Deposition Reactor Using Disilane In Hydrogen. Materials Research Society Symposia Proceedings, 1993, 334, 519.	0.1	0
39	Low pressure chemical vapor deposition of silicon dioxide below 500â€‰Â°C by the pyrolysis of diethylsilane in oxygen. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 625.	1.6	7
40	Selective lowâ€pressure chemical vapor deposition of Si1âˆ'xGexalloys in a rapid thermal processor using dichlorosilane and germane. Applied Physics Letters, 1990, 57, 2092-2094.	1.5	53
41	Characterization of LPCVD of Silicon Nitride in a Rapid Thermal Processor. Materials Research Society Symposia Proceedings, 1989, 146, 345.	0.1	13
42	Low-Pressure Chemical Vapor Deposition of Polycrystalline Silicon and Silicon Dioxide By Rapid Thermal Processing. Materials Research Society Symposia Proceedings, 1989, 146, 109.	0.1	14